

NTB5405N, NVB5405N

MOSFET – Power, Single, N-Channel, D²PAK 40 V, 116 A

Features

- Low $R_{DS(on)}$
- High Current Capability
- Low Gate Charge
- AEC-Q101 Qualified and PPAP Capable – NVB5405N
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Electronic Brake Systems
- Electronic Power Steering
- Bridge Circuits

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V _{DSS}	40	V
Gate-to-Source Voltage			V _{GS}	±20	V
Continuous Drain Current – R _{θJC}	Steady State	T _C = 25°C	I _D	116	A
		T _C = 100°C		82	
Power Dissipation – R _{θJC}	Steady State	T _C = 25°C	P _D	150	W
Continuous Drain Current – R _{θJA} (Note 1)	Steady State	T _A = 25°C	I _D	16.5	A
		T _A = 100°C	I _D	11.6	
Power Dissipation – R _{θJA} (Note 1)	Steady State	T _A = 25°C	P _D	3.0	W
Pulsed Drain Current	t _p = 10 μs		I _{DM}	280	A
Operating Junction and Storage Temperature			T _J , T _{STG}	–55 to 175	°C
Source Current (Body Diode) Pulsed			I _S	75	A
Single Pulse Drain-to Source Avalanche Energy – (V _{DD} = 50 V, V _{GS} = 10 V, I _{PK} = 40 A, L = 1 mH, R _G = 25 Ω)			EAS	800	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T _L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	1.0	$^\circ\text{C/W}$
Junction-to-Ambient (Note 1)	$R_{\theta JA}$	50	$^\circ\text{C/W}$

1. Surface mounted on FR4 board using 1 sq in pad size, (Cu Area 1.127 sq in [2 oz] including traces).

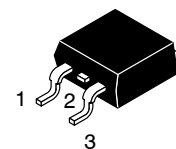
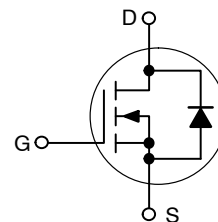


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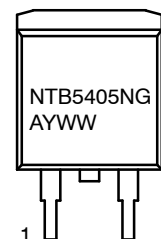
$V_{(BR)DS}$	$R_{DS(ON)}$ TYP	I_D MAX (Note 1)
40 V	4.9 m Ω @ 10 V	116 A

N-Channel



D²PAK
CASE 418B
STYLE 2

MARKING DIAGRAM



NTB5405N = Specific Device Code
G = Pb-Free Device
A = Assembly Location
Y = Year
WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping†
NTB5405NG	D ² PAK (Pb-Free)	50 Units / Rail
NTB5405NT4G	D ² PAK (Pb-Free)	800 / Tape & Reel
NVB5405NT4G	D ² PAK (Pb-Free)	800 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	40			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			39		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 40 V	T _J = 25°C		1.0	μA
			T _J = 100°C		10	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±30 V			±100	nA

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	1.5		3.5	V
Gate Threshold Temperature Coefficient	V _{GS(TH)} /T _J			-7.0		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 40 A		4.9	5.8	mΩ
		V _{GS} = 5.0 V, I _D = 15 A		7.0	8.0	
Forward Transconductance	g _{FS}	V _{GS} = 10 V, I _D = 15 A		32		S

CHARGES AND CAPACITANCES

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 32 V		2700	4000	pF
Output Capacitance	C _{OSS}			700	1400	
Reverse Transfer Capacitance	C _{RSS}			300	600	
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 10 V, V _{DS} = 32 V, I _D = 40 A		88		nC
Threshold Gate Charge	Q _{G(TH)}			3.25		
Gate-to-Source Charge	Q _{GS}			9.5		
Gate-to-Drain Charge	Q _{GD}			37		

SWITCHING CHARACTERISTICS, V_{GS} = 10 V (Note 3)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = 10 V, V _{DD} = 32 V, I _D = 40 A, R _G = 2.5 Ω		8.5		ns
Rise Time	t _r			52		
Turn-Off Delay Time	t _{d(OFF)}			55		
Fall Time	t _f			70		

SWITCHING CHARACTERISTICS, V_{GS} = 5 V (Note 3)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = 5 V, V _{DD} = 20 V, I _D = 20 A, R _G = 2.5 Ω		19		ns
Rise Time	t _r			153		
Turn-Off Delay Time	t _{d(OFF)}			32		
Fall Time	t _f			42		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 20 A	T _J = 25°C		0.82	1.1	V
			T _J = 100°C		TBD		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _{SD} /dt = 100 A/μs, I _S = 20 A		66		ns	
Charge Time	t _a			35			
Discharge Time	t _b			31			
Reverse Recovery Charge	Q _{RR}			113			nC

- Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

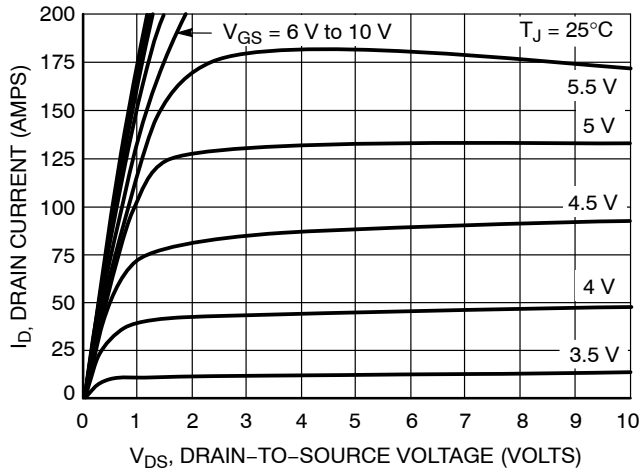


Figure 1. On-Region Characteristics

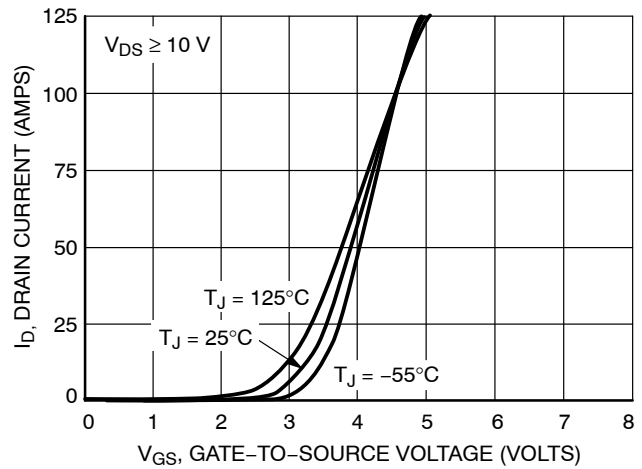


Figure 2. Transfer Characteristics

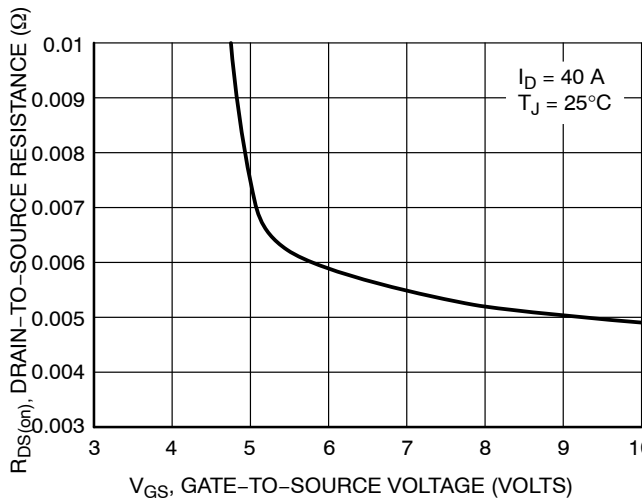


Figure 3. On-Resistance vs. Gate-to-Source Voltage

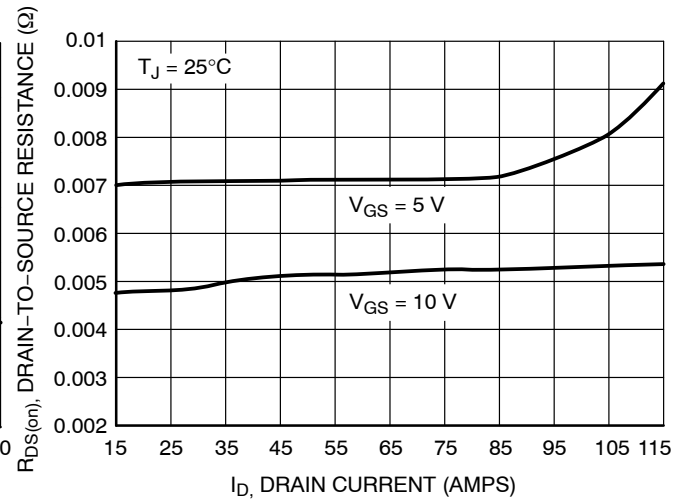


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

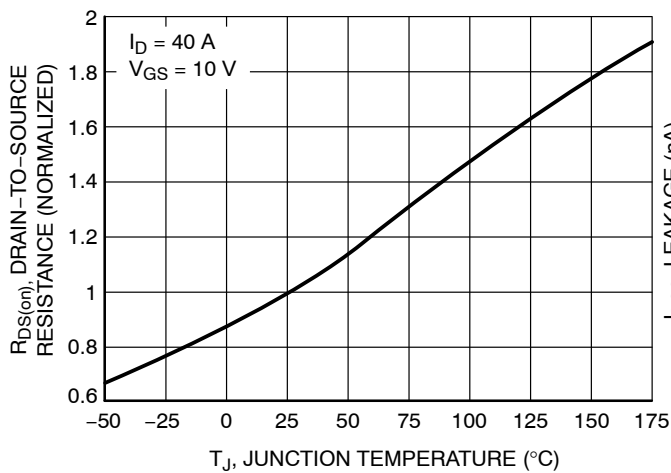


Figure 5. On-Resistance Variation with Temperature

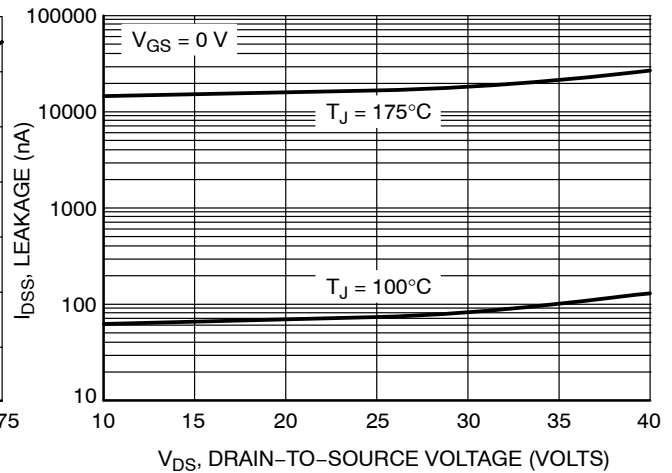
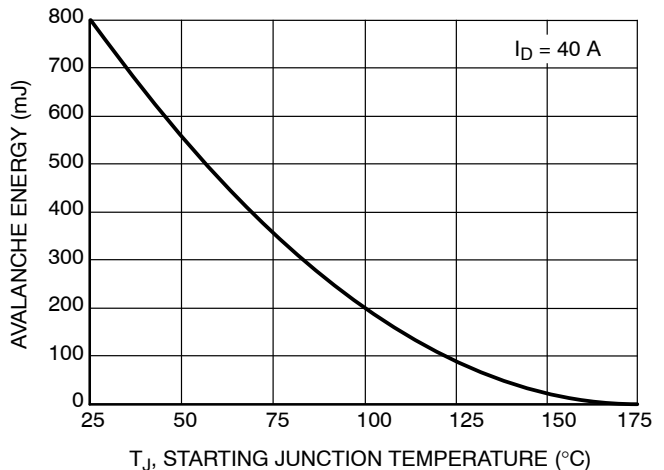
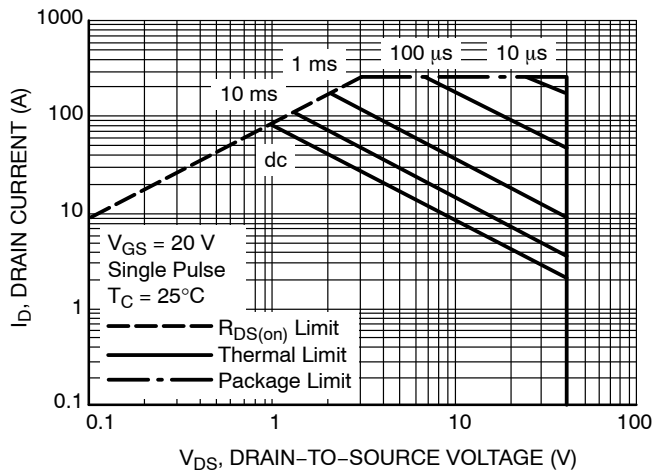
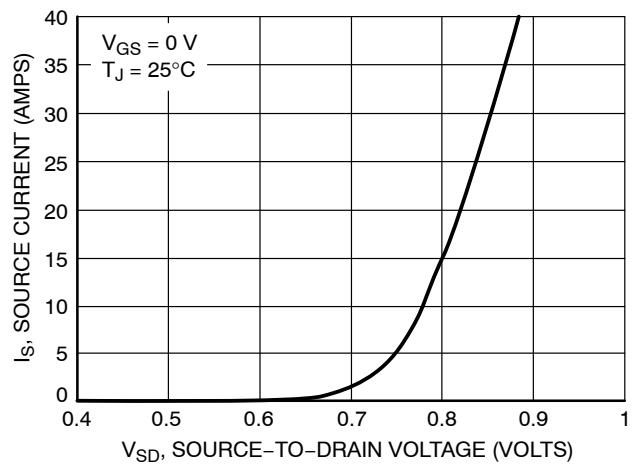
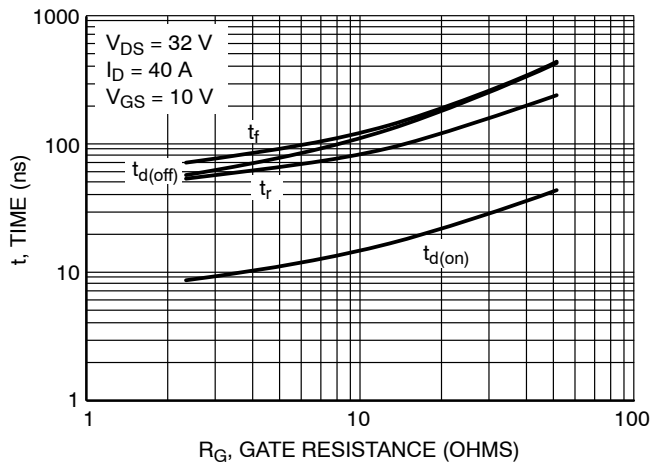
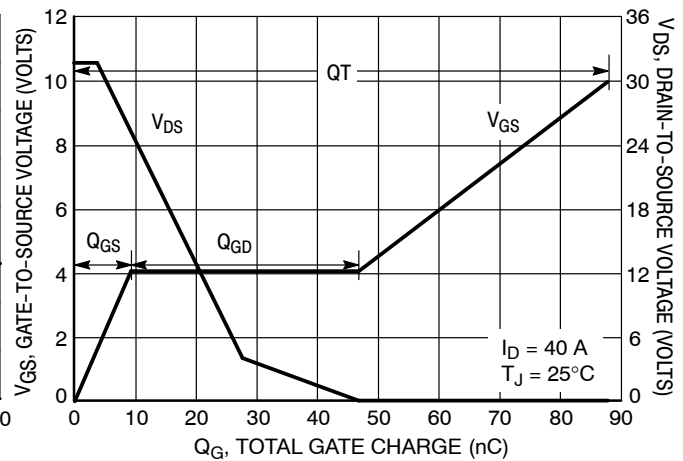
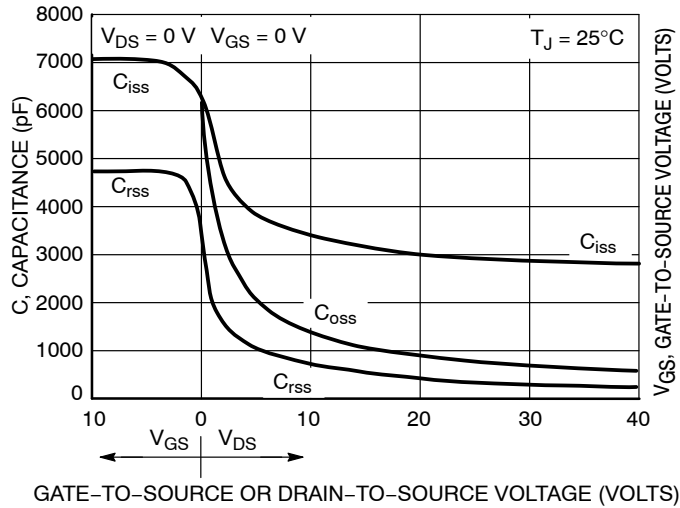


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CURVES



TYPICAL PERFORMANCE CURVES

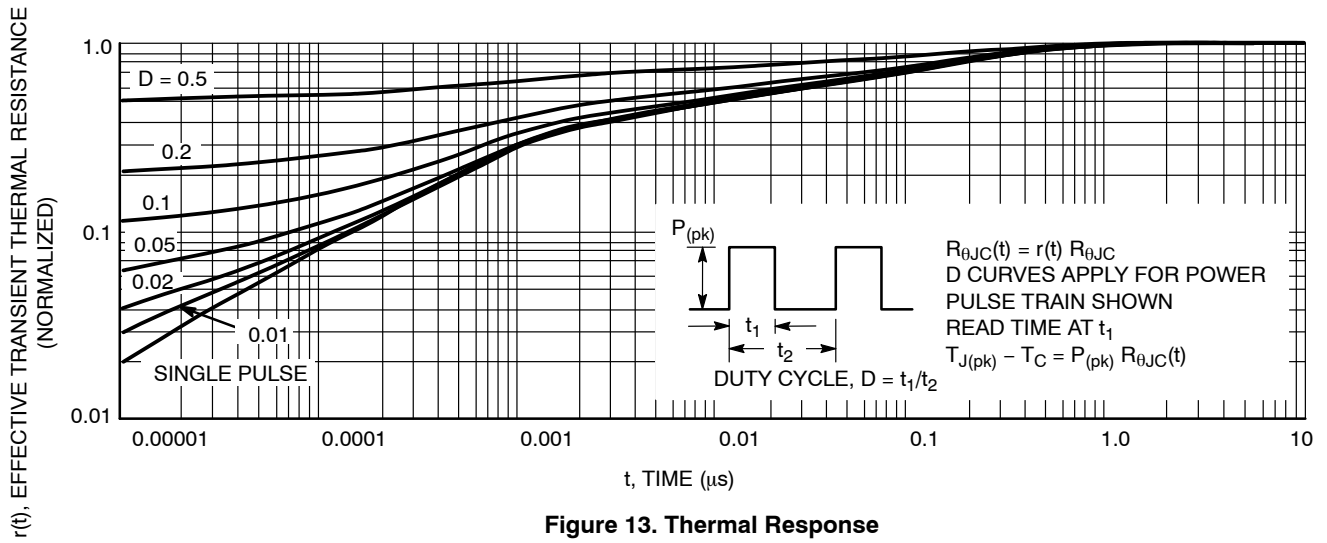
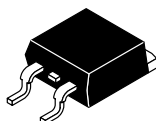


Figure 13. Thermal Response

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

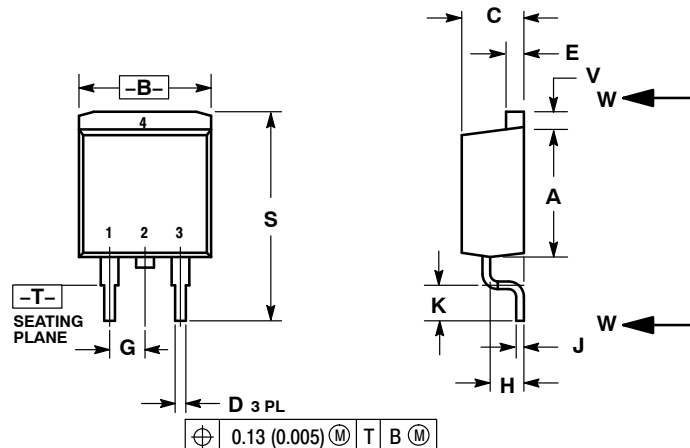
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D²PAK 3
CASE 418B-04
ISSUE L

DATE 17 FEB 2015

SCALE 1:1

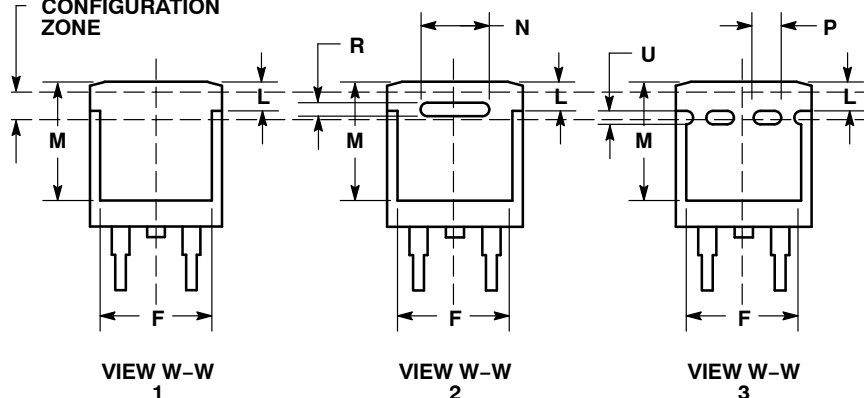


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100 BSC		2.54 BSC	
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197 REF		5.00 REF	
P	0.079 REF		2.00 REF	
R	0.039 REF		0.99 REF	
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40

VARIABLE CONFIGURATION ZONE



STYLE 1:

- PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:

- PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 3:

- PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 4:

- PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 5:

- PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

STYLE 6:

- PIN 1. NO CONNECT
2. CATHODE
3. ANODE
4. CATHODE

MARKING INFORMATION AND FOOTPRINT ON PAGE 2

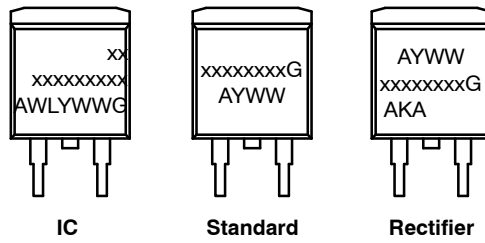
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ISSUE L

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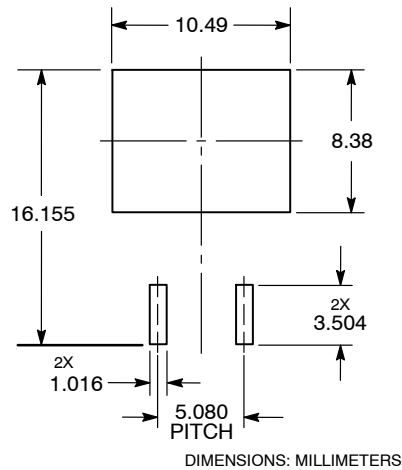
**GENERIC
MARKING DIAGRAM***



xx = Specific Device Code
A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb-Free Package
AKA = Polarity Indicator

*This information is generic. Please refer to device data sheet for actual part marking.
Pb-Free indicator, "G" or microdot "▪", may or may not be present.


SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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